PANJAB UNIVERSITY, CHANDIGARH-160014 (INDIA)

(Estd.under the Panjab University Act VII of 1947-enacted by the Govt. of India)

FACULTY OF ENGINEERING & TECHNOLOGY

SYLLABI

AND THE

REGULATIONS

FOR

M.Tech. (Microelectronics) 2019-20

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SCHEME OF EXAMINATION FOR MASTER OF TECHNOLOGY (MICROELECTRONICS) **Scheme of Examination 2019-20**

FIRST SEMESTER

S.No	Course	Course	Scheme of Teaching		Sc	theme of Exam	ination		
	Code	Name	Contact Credits Theory			Practical*			
			L-T-P	hrs/week		Internal	University	Total	
						Assessment	Assessment		
1	MIC	Semiconductor	3-0-2	5	3+1	50	50	100	50
	101	Device physics							
2	MIC	Integrated	3-0-2	5	3+1	50	50	100	50
	102	Circuit							
		Technology							
3	MIC	MOS Integrated	3-0-2	5	3+1	50	50	100	50
	103	Circuit							
		Modeling							
4	MIC	HDL and VLSI	3-0-2	5	3+1	50	50	100	50
	104	Design							
5		Elective- I	3-0-2	5	3+1	50	50	100	50
6	MIC	Research	0-0-3	3	1				50
	108	Seminar- I							
	T	otal	15-0-13	28	21	250	250	500	300

^{*} Practical marks are for continuous and end semester evaluation

Total Marks: 800 Total Credits: 21

Elective-I

Computer Aided Design Methodologies and Tools MIC 105 Material Science & Engineering Embedded System Design MIC 106

MIC 107

SECOND SEMESTER:

S.No	Cour	Course	Scheme of Teaching			Scheme of Examination			
	se	Name		Contact	Credits	s Theory			Practical*
	Code		L-T-P	hrs/week		Internal	University	Total	
						Assessment	Assessment		
1	MIC	Measurement and	3-0-2	5	3+1	50	50	100	50
	201	Characterization							
		Techniques.							
2	MIC	Architecture of	3-0-2	5	3+1	50	50	100	50
	202	VLSI System.							
3	MIC	Analog and Mixed	3-0-2	5	3+1	50	50	100	50
	203	Signal Device							
		Design.							
4	MIC	Advanced Memory	3-0-2	5	3+1	50	50	100	50
	204	Technology and							
		Design.							
5		Elective- II	3-0-2	3	3+1	50	50	100	50
6	MIC	Research Seminar-II	0-0-3	3	1				50
	208								
		Total	15-0-	26	21	250	250	500	300
			13						

^{*} Practical marks are for continuous and end semester evaluation

Total Marks: 800 Total Credits: 21

Elective- II

MIC 205 Digital Integrated Circuits and Systems

MIC 206 MEMS and Microsystems

MIC 207 RF and High Speed Digital Design

THIRD SEMESTER

S.No	Course	Course	Sch	Scheme of Teaching		Scheme of Examination			
	Code	Name		Contact	Credits		Theory		Practical*
			L-T-P	hrs/week		Internal	University	Total	-
						Assessment	Assessment		
1		Elective- III	3-0-2	5	3+1	50	50	100	50
2		Elective- IV	4-0-0	4	4	50	50	100	
3	MIC	Preliminary	0-0-20	20	10				100
	304	Thesis							
	Total		7-0-22	29	18	100	100	200	150

^{*} Practical marks are for continuous and end semester evaluation

Total Marks: 350 Total Credits = 18

Elective- III

MIC 301 Low Power Digital CMOS Design
MIC 302 Microelectronic Packaging and Testing

Elective- IV

MIC 303 Nano Scale Devices and Systems

MIC 305 Research Methodology

FOURTH SEMESTER:

S.No	Course	Course	Scheme of Teaching		Scheme of Examination			
	Code	Name			Credits		Practical Ma	rks
			L-T-P	hrs/week		Internal	University	Total
						Assessment	Assessment	
1	MIC 401	Thesis	0-0-25	25	15	100	100	200
	T	otal	0-0-25	25	15	100	100	200

^{*} Practical marks are for continuous and end semester evaluation

Total marks: 200 Credits = 15

Internal Assessment of Thesis (MIC 401) will be graded as follows:

S.	Grade	Requirement
No.		
1.	A+	Publication from Thesis in SCI/SCIE indexed Journal
2.	A	Publication from Thesis in Scopus/ESCI indexed Journal
3.	B+	Publication from Thesis in Proceedings of International/
		National Conference

Total M.Tech. Marks: 2150 Total M.Tech. Credits: 75

FIRST SEMESTER

Course Code	MIC-101
Course Title	SEMICONDUCTOR DEVICE PHYSICS
Type of Course	Core
LTP	3 0 2
Credits	4
Course Assessment Methods	
End Semester Assessment (University Exam.)	50
Continuous Assessment (Sessional, Assignments,	50
Quiz)	

SYLLABUS

Note for Examiner- Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt at least two questions from each part.

SECTION-A

Properties of Semiconductor Physics: Energy Bands in Metals, Semiconductors, and Insulators, Direct and Indirect Semiconductors, Variation of Energy Bands with Alloy Composition, Electrons and Holes, Effective Mass, charge carriers in semiconductor, Extrinsic and intrinsic semiconductor, Electrons and Holes in Quantum Wells, Carrier Concentration,

(6)

Carrier Transport Phenomena: Carrier Drift ,Carrier Diffusion ,Graded Impurity Distribution, The Hall Effect, Semiconductor equations and carrier statistics: Poisson's and continuity equations; Introduction to quantum theory of solids: Fermi-Dirac statistics and Boltzmann approximation to the Fermi-Dirac statistics; Semiconductor Diodes; (6)

Non-equilibrium Excess Carriers in Semiconductors: Carrier Generation and recombination, Characteristics of Excess Carriers, Ambipolar Transport ,Quasi-Fermi Energy Levels, Excess-Carrier Lifetime ,Surface Effects. (6)

The p-n Junction: Base structure of the p-n Junction, p-n Junction current, Barrier formation in metal-semiconductor junctions, Semiconductor model, Generation and Recombination currents, Junction break down, charge storage and transients. (5)

SECTION-B

Semiconductor Hetero- junctions: CV characteristics and dopant profiling, IV characteristics, Small signal models of diodes . Energy band diagrams. (4)

Bipolar Transistors: BJT action, minority carrier distribution, low frequency CB current gain, equilibrium circuit Models. (6)

Junction Field Effect Transistor: JFET concepts, device characteristics, non-ideal effects, equivalent circuit and frequency limitation. (6)

Metal Oxide Semiconductor Field Effect Transistors: Metal semiconductor ohmic contacts, MOS structure and operation, capacitance -voltage characteristics, small signal equivalent circuits, non-ideal effects. (6)

TEXT	TEXT BOOKS				
S. No.	Title	Author(s)	Publisher		
1	Solid State Electronic Devices	G. Streetman, and S. K.	7th edition, Pearson		
	Sond State Electronic Devices	Banerjee			
2	Semiconductor Physics and	Neamen, D. Biswas	McGraw-Hill		
	Devices		Education		
RECOM	RECOMMENDED BOOKS				
1	Dhysias of Camicandyston Davises	S. M. Sze and K. N. Kwok	3rd edition, John		
	Physics of Semiconductor Devices		Wiley &Sons		
2	Fundamentals of solid state	C.T. Sah	World Scientific		
	electronics		Publishing Co. Inc		

PRACTICALS:

Course Code	MIC-102		
Course Title	INTEGRATED CIRCUIT TECHNOLOGY		
Type of Course	Core		
LTP	3 0 2		
Credits	4		
Course Assessment Methods			
End Semester Assessment (University Exam.)	50		
Continuous Assessment (Sessional, Assignments,	50		
Quiz)			

Note for Examiner- Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt at least two questions from each part.

SECTION-A

Goals of semiconductor manufacturing: Cost, Quality, Variability, Yield, Reliability. Monolithic IC Processes: Silicon Wafer preparation, wafer cleaning techniques, defects, clean room concept, Unit processes: diffusion systems, Ion implantation, thermal oxidation, photolithography, fine-line lithography, etching, Epitaxy, Chemical Vapour Deposition(CVD) techniques for deposition of polysilicon, silicon dioxide, silicon nitride and metal films, Metallization, Crystal growth and wafer preparation. (12)

Mask generation, Metal film deposition: Evaporation and sputtering techniques. Failure mechanisms in metal interconnects, Plasma and Rapid Thermal Processing: PECVD, Plasma etching and RIE techniques, RTP techniques for annealing, growth and deposition of various films for use in ULSI. Process integration for NMOS, CMOS and Bipolar circuits, Advanced MOS technologies, IC Packaging: IC Packaging: Die Separation, Package Types, Attachment Method.

SECTION-B

Monolithic Components: Bipolar IC process, p-n junction isolation, monolithic bipolar transistor construction, dielectric isolation; MOS device fabrication techniques; CMOS FET technologies: SOS CMOS Process, Twin well CMOS Process, Problems in CMOS process. (12)

Process modeling: Regression Modeling, Single-Parameter Model, Two-Parameter Model, Residuals, Standard Error, Analysis of Variance, Precision of Estimates, Linear Model with Nonzero Intercept, Multivariate Models, Nonlinear Regression, Regression Chart. (11)

TEXT	BOOKS		
S. No.	NAME	AUTHOR(S)	PUBLISHER
1.	VLSI Technology	S. M. Sze	McGraw Hill
2.	Silicon VLSI Technology	James D. Plummer and	Pearson Education
		Micheal D. Deal	
RECOM	IMENDED BOOKS		
1.	Fundamentals of Semiconductor	Gary S.May, S.M.Sze	Wiley Publications
	Fabrication		
2.	Fundamentals of Semiconductor	Gary S. May, Costas J.	A JOHN WILEY &
	Manufacturing and Process	Spanos	SONS, INC.,
	Control		PUBLICATION
3.	Semiconductor Material and	Dieter K. Schroder	Wiley Publications
	device characterization		
4.	ULSI Technology	C.Y. Chang and S.M. Sze	McGraw Hill
			Companies Inc,
			1996

Practical:

- 1. Introduction to process simulation tools, e.g. SUPREM, MINIMOS, STEPS etc.
- 2. Simulation of typical MOS processes and MOSFET Characteristics, extraction of parameters for circuit simulation.

Course Code	MIC-103
Course Title	MOS INTEGRATED CIRCUIT
	MODELLING
Type of Course	Core
LTP	302
Credits	4
Course Assessment Methods	
End Semester Assessment (University Exam.)	50
Continuous Assessment (Sessional, Assignments,	50
Quiz)	

Note for Examiner- Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt at least two questions from each part.

SECTION-A

MOS Transistor : The Metal oxide Semiconductor Structure, The MOS system under external Bias, Structure and Operation of MOS Transistor, MOSFET current-voltage Characteristics, MOSFET Scaling and Small-Geometry effects, MOSFET, level 1 Model Equation and parameters. (10)

MOS Inverter Static Characteristics: Introduction, Resistive-Load Inverter, Inverter with n-Type MOSFET Load, CMOS Inverter. (6)

CMOS Inverter Switching Characteristics: Introduction, Delay-Time Definitions, Calculation of Delay Times, Inverter Design with Delay Constraints. (6)

SECTION-B

Combinational MOS Logic Circuits: Introduction, MOS Logic Circuits with Depletion nMOS Loads, CMOS Logic Circuits, Complex Circuits, CMOS Transmission Gates (Pass Gates), BiCMOS logic. (8)

Sequential MOS Logic Circuits: Introduction, Behavior of Bistable Elements, SR Latch Circuit, Clocked Latch and Flip-Flop Circuits, CMOS D-Latch and Edge-Triggered Flip-Flop.

(6)

Dynamic Logic Circuits: Introduction, Basic Principles of Pass Transistor Circuits, Voltage Bootstrapping, Synchronous Dynamic CMOS Circuit Techniques, High-Performance Dynamic CMOS Circuits. (8)

TEXT 1	BOOKS					
S. No.	NAME	AUTHOR(S)	PUBLISHER			
1.	CMOS Digital Integrated Circuit	Sung-Mo Kang and	TATA McGraw Hill			
	Analysis and Design	Yusuf Leblebici				
RECOM	RECOMMENDED BOOKS					
1	Introduction to VLSI Systems	Mead and Convey	Addison Wesley. 1982			
2	VLSI Design Techniques for Analog and Digital Circuits	Randall Geiger	McGraw Hill.2000			
3	Operation and Modeling of the MOS Transistor	Yannis Tsividis	McGraw Hill International Edition, 1999			
4	Digital Integrated Circuits	Jan M. Rabaey	Prentice Hall of India, (New Delhi), 1997.			

PRACTICALS

- Simulation using schematic editor
- Schematic page editor. Part editor, programmer's editor,
- Session Log editing properties- spreadsheet editor property editor.
- Hierarchical design- Hierarchical blocks, ports, pins
- Placing, editing and connecting parts
- Editing and adding graphics
- Configuring a macro
- Creating a netlist
- Exporting and importing schematic data
- Editing and creating models
- Simulation Parameters
- D.C Sweep Analysis, Transient Analysis, Parametric Analysis and Performance Analysis

Course Code	MIC-104
Course Title	HDL AND VLSI DESIGN
Type of Course	Core
LT P	302
Credits	4
Course Assessment Methods	
End Semester Assessment (University Exam.)	50
Continuous Assessment (Sessional,	50
Assignments, Quiz)	

Note for Examiner- Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt at least two questions from each part.

SECTION-A

Introduction To Hardware Design: Digital System Design Process, Hardware Description Languages, Hardware Simulation, Hardware Synthesis, Levels of Abstraction. (5)

VHDL Background: VHDL History, Existing Languages, VHDL Requirements, The VHDL Language. (5)

Design Methodology Based on VHDL: Elements of VHDL, - Data objects- Variable signal, and constant, Data types, Operators and signal assignments, Design Suits- Entities, architecture declaration, configurations, Packages, Top down Design, Top down Design with VHDL, Subprograms, VHDL Operators, Conventions and Syntax. (8)

Basic Concepts In VHDL: Characterizing Hardware Languages, Objects and Classes, Signal Assignments, Concurrent and Sequential Assignments. (4)

SECTION-B

Design Organization: Definition and Usage of Subprograms, Packaging Parts and Utilities, Generic and configuration, Design Configuration and Libraries. (6)

Utilities For High-Level Descriptions : Type Declarations , VHDL Operators, Subprogram Parameter Types and Overloading, Predefined Attributes, User Defined Attributes. (6)

Behavioral Description of Hardware: Process Statement, Assertion Statement, Sequential Wait Statements. (5)

Verilog: Overview of Digital design with Verilog HDL, basic concepts, modules & ports. (6)

TEXT 1	TEXT BOOKS			
S. No.	NAME	AUTHOR(S)	PUBLISHER	
1	VHDL	Douglas Perry	Tata Mc Graw Hill	
			2004	
RECOM	IMENDED BOOKS			
1	VHDL Analysis & Modelling of	Navabi Z	McGraw Hill.2002	
	Digital system			
2	VHDL for Designers	sjoholm and Lindh	Prentice Hall	
			International,1998	
3	Digital system Design using	Roth. C.H.	Thomson	
	VHDL		learning,2000	

PRACTICALS:

Course Code	MIC-105
Course Title	COMPUTER AIDED DESIGN METHODOLOGIES AND TOOLS
Type of Course	Core
LTP	302
Credits	4
Course Assessment Methods	
End Semester Assessment (University Exam.)	50
Continuous Assessment (Sessional, Assignments,	50
Quiz)	

Note for Examiner- Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt at least two questions from each part.

SECTION-A

Introduction to VLSI design methodologies and supporting CAD tool environment. Overview of C and Data structures, Graphics and CIF, concepts and structure and algorithms for some of the CAD tools.

(9)

Introduction to Unix/Linux, Introduction to SPICE application of SPICE for analog design, writing netlist design and circuit simulation using NGSPICE, Introduction to Layout Tool and IC Layout Design,, Introduction to Physical Verification (LVS, DRC and PEX) Post Layout Simulation with circuit example. (12)

SECTION-B

Schematic editors, layout editors, Module generators, silicon compliers, placement and routing tools. (12)

Behavioral, functional, logic and circuit simulators, Aids for test vector generation and testing. Introduction to Verilog/VHDL languages, behavior level, gate level and dataflow Modeling; RTL coding, logic synthesis and static timing analysis. Design Verification using Test benches. FPGA Design Flow Altera Quartus II. (12)

(Project using CAD tools)

TEXT	TEXT BOOKS			
S. No.	NAME	AUTHOR(S)	PUBLISHER	
1	Computer Aids for VLSI	Steven M. Rubin	Addison-Wesley,	
			1980	
RECOM	RECOMMENDED BOOKS			
1	Algorithms for VLSI Design Automation	Sabin H.Gerez	John Wiley. 2000	
2	An introduction to VLSI Physical design	Majid Serafzadeh	McGraw Hill.2002	
3	Application specific integrated circuits	Michael John Sabastian	Smith Pearson Education (LPE).2001Edition, 1999	

PRACTICAL

Study of

- schematic,
- layout editors,
- layout of gates, cells,
- layout optimization,
- use of silicon compliers.

Course Code	MIC-106
Course Title	MATERIAL SCIENCE & ENGINEERING
Type of Course	Core
LTP	302
Credits	4
Course Assessment Methods	
End Semester Assessment (University Exam.)	50
Continuous Assessment (Sessional,	50
Assignments, Quiz)	

Note for Examiner- Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt at least two questions from each part.

SECTION-A

Material Science: Introduction, processing & selecting materials, looking at Materials by Powers of Ten. Atomic Bonding: Atomic Structure, The Ionic Bond, The Covalent Bond, The Metallic Bond, The Secondary or van der Waals, Bond Materials-The Bonding Classification.

(7

Crystalline Structure & Defects: Metal Structures, Ceramic Structures, Polymeric Structures, Semiconductor Structures, Lattice Positions, Directions, and Planes. Point Defects, Linear Defects, Planar Defects-Two Dimensional Imperfections Non-crystalline Solids- Three Dimensional Imperfections. Thermal Production of Point Defects, Solid State Diffusion, Steady- State Diffusion, Alternate Diffusion Paths (8)

Mechanical and Thermal Behavior: Mechanical: Stress versus Strain, Elastic Deformation, Plastic Deformation, Hardness, Creep and Stress Relaxation, Viscoelastic Deformation. Thermal: Heat Capacity, Thermal Expansion, Thermal Conductivity, Thermal Shock, Failure Analysis and Prevention (7)

SECTION-B

Phase Diagrams: The Phase Rule, the Phase Diagram, the Lever Rule, Heat Treatment, Time the Third Dimension the TTT Diagram, Hardenability, Precipitation Hardening Annealing, The Kinetics of Phase transformations for Nonmetals. (6)

Structural Materials & Processing: Metals, Ceramics, and Glasses, Polymers and Composites, Processing all four Structural Materials, Electronic Materials: Charge Carriers and Conduction, Energy Levels and Energy Bands, Conductors, Insulators, Semiconductors, Composites, Electrical Classification of Materials (6)

Optical and Magnetic Materials: Optical Materials, Magnetic Materials, Materials in Engineering Design, Selection of Electronic, Optical, and Magnetic Materials (5)

Advanced Semiconductor Materials: Band structure, carrier concentration, Electrical Mechanical and optical properties of Gallium Nitride, Aluminium Nitride, Indium Nitride, Boron Nitride, Silicon Carbide, Silicon-germanium (Sil-xGex), Materials of special applications viz. cryogenic, high temperature, high frequency Applications. (6)

TEXT BOOKS				
S. No.	NAME	AUTHOR(S)	PUBLISHER	
1	Properties of Advanced	Michael E .Levinshtein	Springer. 2001	
	Semiconductor Materials: Gan,			
	Aln, Inn			
RECOM	RECOMMENDED BOOKS			
1	Introduction to Materials Science	James F. Shackelford	Prentice Hall.2001	
	for Engineers, 6 th Edition			
2	Fundamentals of Semiconductors:	Yu and M Cardona	Springer, 1996	
	Physics and Materials properties			

PRACTICALS:

Course Code	MIC-107	
Course Title	EMBEDDED SYSTEM DESIGN	
Type of Course	Core	
LT P	302	
Credits	4	
Course Assessment Methods		
End Semester Assessment (University Exam.)	50	
Continuous Assessment (Sessional,	50	
Assignments, Quiz)		

Note for Examiner- Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt any two questions from each part.

SECTION-A

Introduction: A system, processors and other hardware units for embedded systems, Embedded into system, microprocessor, microcontroller, single processor; regular processors and microcontrollers for embedded systems. Examples of Embedded System. (4)

Hardware Aspects: Embedded microcontroller cores, Brief discussion about processor structure: GPP, ASISP, System Processor, Application specific system processor; registers; memories: RAM, ROM, UVROM, EEPROM, Flash Memory, DRAM; parallel and serial communication and ports; timers and interrupts. (8)

Programming Tools and handheld Devices: Using embedded C++, use of RTOS μc/os-I I, use of RTOS VxWorks, Kernel of an embedded system and device drivers. (12)

SECTION-B

Using Multiple Processors in Embedded Systems: Multiple process in parallel, modelling tools for a multiprocessor system, distributed embedded systems, Systems on chip(SOC). (8)

Design of an embedded system: System design, design cycle development phase for an embedded system, users of target systems, emulator and ICE, use of software tools for embedded systems, scopes and analyzers for system hardware test; Technological aspects of embedded systems: interfacing between analog and digital blocks, signal conditioning, digital signal processing. (13)

TEXT BOOKS				
S. No.	NAME	AUTHOR(S)	PUBLISHER	
1	Embedded Systems	Raj Kamal	Tata Mcgraw Hill. 2004	

REC	OMMENDED BOOKS		
1	Embedded System Design	Frank Vahid & Tony Givargis	John Wily & Sons.1998
2	Embedded System Design – An Introduction to Processes, Tools & Techniques	Arnold S. Berger	CMP Books.2000
3	Real Time Systems	W.S. Liu Jane	Pearson Education.2003
4	Specification and Design Methodology for Real Time Embedded Systems	Janka S. Randall	CMP Books.2000
5	The Art of Designing Embedded Systems	Jack Ganssle	Newnes, 1999
6	Embedded Microcomputer System: Real Time Interfacing	J.W. Valvano	Brooks/Cole, 2000

PRACTICALS:

SECOND SEMESTER

Course code	MIC-201
Course Title	MEASUREMENT AND
	CHARACTERIZATION TECHNIQUES
Type of Course	Core
LTP	302
Credits	4
Course Assessment Methods	
End Semester Assessment (University Exam.)	50
Continuous Assessment (Sessional,	50
Assignments, Quiz)	

SYLLABUS

Note for Examiner- Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt at least two questions from each part.

SECTION-A

Introduction to materials and techniques, Structure analysis tools: X-ray diffraction; Reflection High energy electron Diffraction (RHEED), Low energy Electron Diffraction (LEED), Transmission Electron Microscopy (TEM); (8)

Basic Electron scattering, Concepts of resolution, TEM instruments, Various imaging modes, Analysis of micrographs, Electron Energy Loss Spectroscopy; Scanning Electron Microscopy, Rutherford backscattering spectrometry; Atomic Force Microscopy, Scanning Probe Microscopy.

(8)

Electrical Characterization Techniques: Electrical resistivity in bulk and thin films, Hall effect, Magnetoresistance; (7)

SECTION-B

Optical Characterization Techniques: UV-VIS spectroscopy, Fourier transform infrared spectroscopy, Raman spectroscopy, X-ray photoelectron spectroscopy. (8)

Electron Beam Techniques: Electron Beam Induced Current (EBIC) and voltage contrast technique. (6)

Auger Electron Spectroscopy(AES), Electron Microphone (EDX), LEED, RHEED, Ion beam Techniques (SIMS, RBS), X-ray techniques (XPS, X-ray Topography). (8)

TEXT	TEXT BOOKS			
S. No.	NAME	AUTHOR(S)	PUBLISHER	
1	Semiconductor Measurement and	W.R. Runyan	McGraw Hill	
	Instrumentation			
2.	Solid State Electronic Devices	Ben G. Streetman	Pearson,2015	
RECON	RECOMMENDED BOOKS			
1	Imperfections and Impurities in	K.V. Ravi	John Wiley and Sons	
	Semiconductor Silicon			
2	Characterization of Semiconductor	Philip F. Kare and Greydon	Mc-Graw Hill	
	Materials	B. Laubee		

PRACTICALS:

Course Code	MIC-202
Course Title	ARCHITECTURE OF VLSI SYSTEMS
Type of Course	Core
LTP	302
Credits	4
Course Assessment Methods	
End Semester Assessment (University Exam.)	50
Continuous Assessment (Sessional,	50
Assignments, Quiz)	

Note for Examiner- Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt at least two questions from each part.

SECTION-A

Overview of architectural schemes, organization, systems representation: structural, behavioural, data flow; Arithmetic and Logical operation and hardware implementation, Software implementation of some complex operation. Introduction to memory Unit, control unit and Instruction Set, Working with an ALU, Concepts of Machine level programming, Assembly level programming and High level programming. Various addressing modes and designing of an Instruction set, Concepts of subroutine and subroutine call, Use of stack for handling subroutine call and return (8)

Introduction to CPU design, Instruction interpretation and execution, Micro-operation and their RTL specification, Hardwired control CPU design, Microprogrammed control CPU design (8)

Concepts of semiconductor memory, CPU- memory interaction, organization of memory modules, Cache memory and related mapping and replacement policies, Virtual memory (7)

SECTION B

Introduction to input/output processing, working with video display unit and keyboard and routine to control them, Programmed controlled I/O transfer, Interrupt controlled I/O transfer, DMA controller, Secondary storage and type of storage devices, Introduction to buses and connecting I/O devices to CPU and memory. (7)

CISC Vs RISC, Introduction to pipelining and pipeline hazards, design issues of pipeline architecture, Instruction level parallelism and advanced issues, Introduction to interconnection network and practical issues, Examples of interconnection networks. Multiprocessors and its characteristics, Memory organization for multiprocessors systems

(8)

Synchronization and models of memory consistency, Issues of deadlock and scheduling in multiprocessor systems, Cache in multiprocessor systems and related problems, Parallel processing concepts, Parallelism algorithm for multiprocessor systems. (7)

TEXT	TEXT BOOKS			
S. No.	NAME	AUTHOR(S)	PUBLISHER	
1	Computer Architecture and	J.P Hayes	Mc.Graw Hill. 1998	
	Organization			
RECOM	IMENDED BOOKS			
1	Computer Architecture	Nicholas Carter, Schaum's	McGraw Hill.2001	
		outlines		
2	Computer system organization and	Carpinellie	Pearson Education.	
	Architecture		2001	
3	Parallelled Algorithms for VLSI	Prithviraj Banerjee	PTR Prentice Hall.	
	Computer Aided Design		1992	

PRACTICALS:

Course Code	MIC-203
Course Title	ANALOG AND MIXED SIGNAL DEVICE
	DESIGN
Type of Course	Core
LT P	302
Credits	4
Course Assessment Methods	
End Semester Assessment (University Exam.)	50
Continuous Assessment (Sessional,	50
Assignments, Quiz)	

Note for Examiner- Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt at least two questions from each part.

SECTION-A

Basic MOS Device physics: Analog VLSI issues in CMOS technologies, Basic MOS Models, SPICE Models and frequency dependent parameters, Basic NMOS/CMOS Gain stage. (8)

Single stage amplifiers: basic concepts, common-source stage, source follower, common-gate stage, Current sources and sinks. (6)

Passive and Active Current Mirrors: basic current mirrors, cascode current mirrors, active current mirrors, Voltage and current references. (6)

SECTION-B

Differential Amplifier: Single ended and differential operation ,basic differential pair ,common mode response ,differential pair with MOS loads ,Gilbert Cell. (7)

Operational Amplifiers: Basic design parameters of op-amp design. Compensation of op-amp. Basics design concept of 741 op-amp design. MOS Differential amplifier. (8)

CMOS op-amps: Design of CMOS op-amp, design of one stage op-amp. (4)

Analog-to-Digital Converters: serial A/D converters, Successive approximation A/D converters, Analog Multipliers (6)

TEXT BOOKS								
S. No.	NAME				AUTHOR	(S)	PUBLISHE	R
1	CMOS	Analog	Circuit	Design,	Philip	E.Allen,Douglas	Newyork:	Oxford
second edition R.Holberg 2006								

RECOM	MENDED BOOKS		
1	Design of Analog CMOS Integrated Circuits	B. Razavi	McGraw- Hill, 2001.

PRACTICAL

- Simulation of analog integrated circuits
- Simulation & characterization of mixed signal devices

Course Code	MIC-204
Course Title	ADVANCED MEMORY TECHNOLOGY
	AND DESIGN
Type of Course	Core
LTP	302
Credits	4
Course Assessment Methods	
End Semester Assessment (University Exam.)	50
Continuous Assessment (Sessional,	50
Assignments, Quiz)	

Note for Examiner- Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt at least two questions from each part.

SECTION A

INTRODUCTION TO MEMORY CHIP DESIGN: Internal Organization of Memory Chips, Memory cell Array, Peripheral Circuit, I/O Interface categories of Memory Chip, Basic Operation of 1-T Cell, Basic Operation of Flash Memory Cells, Advances in Flash-Memory Design and Technology. (8)

BASICS OF RAM DESIGN AND TECHNOLOGY: Devices, NMOS Static Circuits, NMOS Dynamic Circuits, CMOS Circuits, Basic Memory Circuits, Scaling Law. (8)

ON-CHIP VOLTAGE GENERATORS: Substrate-Bias Voltage(VBB) Generator, Voltage Up-converter, Voltage Down-Converter, Half-VDD Generator, Examples of Advanced On-chip Voltage Generators. (8)

SECTION B

DRAM CIRCUITS: High-Density Technology, High-Performance Circuits, Catalog Specification of the Standard DRAM, Basic Configuration and Operation of the DRAM Chip, Chip Configuration, Address Multiplexing, Fundamental Chip, Multi-divided Data line and Word line, Read and Relevant Circuits, Write and relevant Circuits, Refresh-Relevant Circuits, Redundancy Techniques, On-chip testing Circuits, High Signal-to-Noise ratio DRAM Design and Technology, Trends in High S/N Ratio Design, Data-Line Noise Reduction, Noise Sources.

(11)

HIGH-PERFORMANCE SUBSYSTEM MEMORIES: Hierarchical Memory Systems, Memory-Subsystem Technologies, High-Performance Standard DRAMs, Embedded Memories. (10)

TEXT 1	TEXT BOOKS			
S. No.	NAME	AUTHOR(S)	PUBLISHER	
1	Semiconductor Memories:	Ashok K. Sharma	Wiley-IEEE	
	Technology, Testing, and		Press,2002	
	Reliability			
RECOM	MENDED BOOKS			
1	Advanced Semiconductor	Ashok K. Sharma	Wiley-IEEE	
	Memories: Architectures, Designs,		Press,2002	
	and Applications			
2	Semiconductor Memories: A	Betty Prince	Wiley- IEEE Press,	
	handbook of Design, Manufacture		2 nd Edition	
	and Application,			
3	Ferroelectric Memories	James Scot	Springer	
			publications	
4	Flash memories	Paolo Cappelletti, Carla	Academic	
		Golla, Piero Olivo, Enrico	Publishers, Boston	
		Zanoni, Kluwer		
5	Emerging memories, Technologies	Betty Prince	Kluwer Academic	
	and Trends		Publishers.	

PRACTICALS:

Course Code	MIC-205
Course Title	DIGITAL INTEGRATED CIRCUITS &
	SYSTEMS
Type of Course	Core
LT P	302
Credits	4
Course Assessment Methods	
End Semester Assessment (University Exam.)	50
Continuous Assessment (Sessional,	50
Assignments, Quiz)	

Note for Examiner - Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt at least two questions from each part.

SECTION-A

Introduction: Digital Systems; Data representation and coding; Levels of Abstraction, Logic circuits, integrated circuits; Analysis, design and implementation of digital systems. (4)

Combinatorial Logic Systems: Definition and specification; Truth table; Basic logic operation and logic gates. Boolean Algebra and Switching Functions: Basic postulates and fundamental theorems of Boolean algebra; Standard representation of logic functions - SOP and POS forms; Simplification of switching functions - K-map and Quine-McCluskey tabular methods; Synthesis of combinational logic circuits, encoders, Parity circuits and comparators; Arithmetic modules-adders, subtractors and ALU. (10)

Logic families: Operational characteristics of MOSFET as switch; CMOS inverter - circuit description and operation; Structure and operations of CMOS gates; Electrical characteristics of logic gates – logic levels and noise margins, fan-out, propagation delay, transition time, power consumption and power-delay product. (10)

SECTION-B

Sequential Logic systems: State machines, state machine as a sequential controller; Basic sequential circuits- latches and flip-flops: SR-latch, D-latch, D flip-flop, JK flip-flop, T flip-flop; Timing hazards and races; Analysis of state machines using D flip-flops and JK flip-flops; Design of state machines - state table, state assignment, transition/excitation table, excitation maps and equations, logic realization; Design examples (9)

State Machine Design Approach: Designing state machine using ASM charts; Designing state machine using state diagram. (4)

Sequential Logic Modules and Applications: Multi-bit latches and registers, counters, shift register, application examples-. High speed adders, multipliers, FIFOs, and Barrel shifters, ALU control semiconductors for memories and PLAs, microprogrammed and PLA based control design. Programmable Logic Devices: PLAs, PALs and their applications; Sequential PLDs and their applications; State machine design with sequential PLDs; Introduction to field programmable gate arrays (FPGAs)

(8)

TEXT 1	BOOKS		
S. No.	NAME	AUTHOR(S)	PUBLISHER
1	Digital Design: Principle and practices	John F. Wakherly	PHI International, 1994
2.	Principles of Digital Design	Daniel D.Gajski	Prentice Hall
RECOM	IMENDED BOOKS		
1	Digital Circuits: A proportion for Microprocessors	Charles Mckay	Prentice Hall
2	Fundamentals of Digital Circuits	A. Anand Kumar	PHI

PRACTICALS:

Course Code	MIC-206
Course Title	MEMS AND MICROSYSTEMS
Type of Course	Core
LT P	302
Credits	4
Course Assessment Methods	
End Semester Assessment (University Exam.)	50
Continuous Assessment (Sessional,	50
Assignments, Quiz)	

Note for Examiner- Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt at least two questions from each part.

SECTION A

Overview, Working principle of microsensors & microactuation

(4)

Scaling of Forces: 1.1 Scaling of Forces Model, Weight, Example: MEMS Accelerometer, Elastic Force, Example: AFM Cantilever, Electrostatic Force, Example: MEMS RF Switch, Piezoelectric Force. Elasticity: Stress, Strain, Stress—strain Relationship, Example: Plane Stress, Strain—stress Relationship in Anisotropic Materials, Miller Indices, Example: Miller Indices of Typical Planes.

Bending of Microstructures: Static Equilibrium, Free Body Diagram, Neutral Plane and Curvature, Pure Bending, Neutral Plane for a Rectangular Cross-section, Example: Cantilever with Point Force at the Tip, Moment of Inertia and Bending Moment, Example: Moment of Inertia of a Rectangular Cross-section, Beam Equation, End-loaded Cantilever, Equivalent Stiffness, Beam Equation for Point Load and Distributed Load. (10)

SECTION B

Piezoresistance: Electrical Resistance, Example: Resistance Value, One-dimensional Piezoresistance Model, Example: Gauge Factors, Piezoresistance in Anisotropic Materials, Two-dimensional Piezoresistors, Example: Accelerometer with Cantilever and Piezoresistive Sensing, Pressure Sensing with Rectangular Membranes. (8)

Electrostatic Driving and Sensing: Energy and Co-energy, Voltage Drive, Pull-in Voltage, Forces in a Parallel-plate Actuator, Electrostatic Pressure, Contact Resistance in Parallel-plate Switches, Capacitive Accelerometer. (8)

Fabrication: Introduction, Photolithography, Patterning, Lift-off, Bulk Micromachining, Angle of Walls in Silicon (100) Etching, Surface Micromachining, Example: Cantilever Fabrication by Surface Micromachining. (7)

TEXT E	TEXT BOOK				
S. No.	NAME	AUTHOR(S)	PUBLISHER		
1	Understanding MEMS: Principles	Luis Castaner	Wiley Publication,		
	and Applications		2015		
REFER	ENCE BOOK				
1	MEMS & Microsystem- Design & Manufacture	Tai-Ran Hsu	Tata McGraw Hill.2002		

PRACTICALS:

Note for Examiner- Examiner will set 7 questions of equal marks. First question will cover

Course Code	MIC-207
Course Title	RF AND HIGH SPEED DIGITAL DESIGN
Type of Course	Core
LTP	302
Credits	4
Course Assessment Methods	
End Semester Assessment (University Exam.)	50
Continuous Assessment (Sessional,	50
Assignments, Quiz)	

whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt any two questions from each part.

SECTION-A

Introduction to RF and wireless: Complexity comparison, Design bottle necks, Applications, Analog and digital systems, Choice of Technology. Basic Concepts In RF Design: Nonlinearity and time variance, ISI, Random process and noise, sensitivity and dynamic range, conversion gains and distortion, passive impedance transformation. Analog and Digital Modulation for RF circuits: Comparison of various techniques for power efficiency. Coherent and Non coherent defection. (12)

Multiple Access: Techniques and wireless standards, mobile RF communication, FDMA, TDMA, CDMA, Wireless standards. Receiver and Transmitter Architectures and Testing heterodyne, Homodyne, Image-reject, Direct-IF and sub-sampled receivers. Direct Conversion and two steps transmitters. BJT and MOSFET behavior at RF frequencies Modeling of the transistors and SPICE models. Noise performance and limitation of devices. Integrated Parasitic elements at high frequencies and their monolithic implementation. (12)

SECTION B

Transceiver Architecture : General considerations, receiver architecture, Transmitter Architecture, transceiver performance tests, case studies. Amplifiers, Mixers and oscillators LNAs, down conversion mixers, Cascaded Stages, oscillators, Frequency synthesizers. (8)

Power Amplifiers: General considerations, linear and nonlinear Pas, classification, High Frequency power amplifier, large signal impedance matching, linearization techniques. (6)

High speed Design: Ideal transmission line fundamentals, Crosstalk, Non Ideal interconnect issues, connectors packages and vias, Non ideal return paths, simultaneous switching noise, and power delivery, buffer modeling, digital timing analysis, timing specific design methodologies,

radiated emissions compliance and system noise minimization, high speed measurement techniques. (8)

TEXT E	BOOK		
S. No.	NAME	AUTHOR(S)	PUBLISHER
1	High- Speed Digital System	Stephen H.Hall	Springer.2001
	Design		
REFERI	ENCE BOOK		
2	Practical RF Circuit Design for	Les Besser	Rowan Gilmore
	Modern Wireless Systems,		
	Volume I : Passive Circuits and		
	Systems		

PRACTICALS:

THIRD SEMESTER

Course Code	MIC-301
Course Title	LOW POWER DIGITAL CMOS
	DESIGN
Type of Course	Core
LT P	302
Credits	4
Course Assessment Methods	
End Semester Assessment (University Exam.)	50
Continuous Assessment (Sessional, Assignments,	50
Quiz)	

SYLLABUS

Note for Examiner - Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt at least two questions from each part.

SECTION-A

Hierarchy of Limits of Power: Introduction, Theoretical Limits: fundamental limits, material limits, device limits, circuit limits, system limits. (6)

Sources of power consumption: switching component of power-switching energy per transition, activity factor, influence of logic level statistics on activity factor- type of logic function, type of logic style, signal statistics, inter signal co-relations, short circuit component of power, leakage component of power. (8)

Power Estimation, Synthesis for low power- behavioral level, logic level, circuit level, Voltage scaling approaches. (8)

SECTION-B

Design and test of low power circuits, Adiabatic switching, Minimizing switched capacitance. **Low Energy Computing using Energy Recovery Techniques,** (4)

Low Power SRAM Architecture: organization of static RAM,MOS SRAM memory cell operations-4T, 6T,banked organizations of SRAM, reduced voltage swings on bit line, reduced power in -write driver circuit, sense amplifier circuit (8)

Low power Programmable computation: architectural approaches to low power, shutdown techniques, conventional shutdown approaches- rest mode, sleep mode, shutdown mode, predictive shutdown approaches, architectural voltage driven reduction. (7)

Software design for low power: sources of software power dissipation, power estimations, power optimization. (4)

TEXT BOOKS			
S. No.	NAME	AUTHOR(S)	PUBLISHER
1	Low power CMOS VLSI Circuit	Kaushik Roy and Sharat	John Wiley &
	Design	Parsad	Sons.1998
RECOMMENDED BOOKS			
1	Low Power Digital CMOS Design	A.P. Chandrakasan and R	Kluwer Academic
		Brodersen	Publishers. 1995
2	Low Power Design Methodoligies	J.M. Rabaey and M.	KJ Academic
		Pedram	Publishers. 2001
3	Designing CMOS Circuits for	Dimitrios Soudris,	Kluwer Academic
	Low Power	Christian Piguet and Costas	Publishers. 2000
		Goutis	

PRACTICALS:

Course Code	MIC-302	
Course Title	MICROELECTRONICS PACKAGING AND TESTING	
Type of Course	Core	
LT P	302	
Credits	4	
Course Assessment Methods		
End Semester Assessment (University Exam.)	50	
Continuous Assessment (Sessional, Assignments,	50	
Quiz)		

Note for Examiner- Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt at least two questions from each part.

SECTION-A

PACKAGING: Introduction, Packaging Hierarchy, Package parameters, packaging substrates, package types, Hermetic packages, die attachment techniques, package parasitic, package modeling, packaging in wireless application, future trends. (11)

BASICS OF TESTING AND FAULT MODELING Introduction- Principle of testing, types of testing -DC and AC parametric tests, fault modeling, Stuck-at fault, fault equivalence, fault collapsing, fault dominance, fault simulation- Event driven simulation, serial simulation, parallel simulation, concurrent simulation. (12)

SECTION-B

TESTING AND TESTABILITY OF COMBINATIONAL CIRCUITS Test generation basics - Automatic test pattern generation, ATPG algorithm, types of ATPG algorithm, D algorithm , PODEM, Testable combinational logic circuit design. (6)

MEMORY, DELAY FAULT AND IDDQ TESTING Testable memory design - RAM fault models - test algorithms for RAMs – Delay faults - Delay test- IDDQ testing - testing methods - limitations of IDDQ Testing, boundary scan test, boundary scan controller. (8)

BUILT-IN SELF-TEST Test pattern generation of Built-in Self-Test (BIST) – LPSR and MISR. (8)

TEXT	TEXT BOOKS			
S. No.	NAME	AUTHOR(S)	PUBLISHER	
1	Microelectronics Packaging	R.R. Tummals et. al.	Kluwer Academic	
	Handbook: Semiconductor		Publishers	
	Packaging Part I, II, III			
RECOM	RECOMMENDED BOOKS			
1	Circuits, Interconnects &	H.B.Bakoglu	Addison Wesley	
	Packaging for VLSI			
2	Fundamentals of Microfabrication	Marc Madou	CRC Press. 1990	
3	Digital Systems Testing and	Miron Abramovici, Melvin	Jaico publishing	
	Testable design	A. Breuer & Arthur D.	House. 2002	
		Friedman		
4	VLSI Fault Modeling and Testing	G.W.Zobrist	Albex Publishers.	
	Techniques		1995	
5	Testing and Diagnosis of VLSI	F. Lombardi and M. Sami	Kluwer Academic	
	and ULSI		Publishers. 1996	
6	Neural Models and Algorithms for	S.T. Chakradhar, U.D.	Kluwer Academic	
	Digital Testing	Agrawal & M.L Bushnell	Publishers. 1996	
7	Testing and Reliable Design of	N.K. Jha & S. Kurdu	Kluwer Academic	
	CMOS Circuits		Publishers. 1996	

PRACTICALS:

Course Code	MIC-303	
Course Title	NANOSCALE DEVICES AND SYSTEMS	
Type of Course	Core	
LTP	400	
Credits	4	
Course Assessment Methods		
End Semester Assessment (University Exam.)	50	
Continuous Assessment (Sessional,	50	
Assignments, Quiz)		

Note for Examiner- Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt at least two questions from each part.

SECTION A

Nanostructures: Introduction, Progressing technology, macroscopic observables in nanostructures, Ballistic transport, Phase interference, Carrier heating in nanostructures. (10)

Quantum confined systems: Nanostructure materials, Lateral confinement: Quantum wires and quantum dots, Nanolithography, Quantum wire and quantum dot structures, Electronic states in quantum wires and quantum dots, Magnetic field effects in quantum confined systems, Transmission in nanostructures, Tunnelling in planar barrier structures, Wave function treatment of tunnelling, Current in resonant tunnelling diodes, Singleelectron effects and Coulomb Blockade, Introduction to Nano electro mechanical systems (NEMS).

SECTION B

Introduction to Molecular electronic devices, self-assembled monolayers (SAM), Diodes, Optoelectronic Devices, Switches, Nanowires, programmable logic arrays, digital gates, flip-flops, shift registers, memories, rectifiers, Overview of Nano materials. (12)

Nano Fabrication Techniques: Lithography, Self- Assemble, contact imprinting and Binding of organics and semiconductors. (11)

TEXT BOOKS			
S. No.	NAME	AUTHOR(S)	PUBLISHER
1	Transport in Nanostructures	Ferry, David K. and	Cambridge
		Goodnick, Stephen	University Press
		Marshall	
RECOMMENDED BOOKS			
1	Nanotechnology	G. Timp	Bell Labs, Murray
			Hill, NJ (Ed.)
2	Molecular electronic devices, Part	F.L. Carter, Forrest. L	Marcel and Dekker
	II		
3	Nano Systems: Molecular	Eric Drexler	John Wiley and
	machinery, manufacturing and		sons.
	computation		
4	Organic electroluminescent	S Miyata, H.S.Nalwa.	Amsterdam, 1997
	materials and devices	Gordon and breach science	
5	Organic semiconductors	Felix Gutmann, Lawrence	John Wiley & Sons
		Elyons	

PRACTICALS:

Course Code	MIC 305		
Course Title	RESEARCH METHODOLOGY		
Type of Course	Elective		
LTP	4-0-0		
Credits	4		
Course Assessment Methods			
End Semester Assessment (University	50		
Exam.)	50		
Continuous Assessment (Sessional,			
Assignments, Quiz)			

Note for Examiner- Examiner will set 7 questions of equal marks. First question will cover whole syllabus, having 10 conceptual questions of 1 mark each or 5 questions of 2 mark each and is compulsory. Rest of the paper will be divided into two parts having three questions each and the candidate is required to attempt at least two questions from each part.

SECTION-A

(3)

Introduction to Educational Research

Concept, types – basic, applied and action, Need for educational research

Reviewing Literature

Need, Sources – Primary and Secondary, Purposes of Review, Scope of Review, steps in conducting review. (3)

Identifying and Defining Research Problem

Locating, analyzing stating and evaluating problem. Generating different types of hypotheses and evaluating them. (5)

Methods of Research

Descriptive research design - survey, case study, content analysis, Ex-post Facto Research, Correlational and Experimental Research (5)

Sampling Techniques

Concept of population and sample' sampling techniques - simple random sampling, stratified random sampling, systematic sampling and cluster sampling, snow ball sampling, purposive sampling, quota sampling techniques. Determining size of sample. (6)

SECTION-B

Design and Development of Measuring Instruments, Tests, questionnaires, checklists, observation schedules, evaluating research instruments, selecting a standardized test. (6)

Procedure Of Data Collection

Aspects of data collection, coding data for analysis

(3)

Statistical Methods of Analysis

Descriptive statistics: Meaning, graphical representations, mean, range and standard deviation, characteristics and uses of normal curve.

Inferential statistics: t-test, Chi-square tests, correlation (rank difference and product moment), ANOVA (one way), Selecting appropriate methods. (7)

Procedure for Writing a Research Proposal

Purpose, types and components of research proposal.

(3)

Procedure for Writing a Research Report

Audiences and types of research reports, Format of research report and journal articles. (2)

Strategies for Evaluating, Research disseminating and utilizing research – An Overview (2)

Practice Tasks

- Define a research problem in polytechnic education/industry after studying problem situation and literature
- Given the purpose, objectives of research, write hypotheses
- Select research designs for the given research objectives
- Identify the measuring instruments for the given research objectives/hypotheses
- Identify the appropriate statistical methods of analysis for the given research proposal.
- Critically analyse the given research reports on various aspects such as hypothesis, design, measuring tools, statistical analysis, interpretation etc. to identify the gaps or weaknesses in the study.

TEXT BOOKS			
S. No.	NAME	AUTHOR(S)	PUBLISHER
1	Educational Research: An Introduction	Borg, W and Gall,M.	New York, Longman.2003
2	Educational Research in Classrooms	Cohen, L.	Harper and Row
	and Schools! A Manual of Materials		Publishers.2000
	and Methods NY		
3	CPSC: Developing Skills in Technician	Colombo Plan Staff	
	Education Research Modules 1 to 11	College for	
	Singapore	Technician Education	
4	Statistics in Psychology and Education,	Garrett, HE and	Vakils Fetter and Simons
	Educational Research, Bombay	Woodworth, RS.	Ltd. 2003
5	Educational Research, Ohio	Gay, LR	Charles E. Merril
			Publishing Company2000.
6	Wiersma William Research Methods in	Allyn and Bacon	Inc.2000
	Education – An Introduction London		

Preliminary Thesis and Thesis

Each student will be required to work on the Preliminary Thesis and Thesis approved by department faculty that will span III and IV semesters during which periodic progress reports will be monitored. At the end of III semester, Preliminary Thesis progress will be evaluated by the departmental faculty.

At the end of IV semester, the student will submit the Thesis.